Pierre Lefebvre

List of Publications by Year in Descending Order

187 papers	4,848 citations	38 h-index	62 g-index
197 ext. papers	5,050 ext. citations	2.7 avg, IF	4.7 L-index

#	Paper	IF	Citations
187	Trapping Dipolar Exciton Fluids in GaN/(AlGa)N Nanostructures. *Nano Letters*, **2019**, 19, 4911-4918	11.5	2
186	Switching of exciton character in double InGaN/GaN quantum wells. *Physical Review B*, **2018**, 98,	3.3	8
185	Room-Temperature Transport of Indirect Excitons in (Al,Ga)N/GaN Quantum Wells. *Physical Review Applied*, **2016**, 6,	4.3	16
184	Picosecond dynamics of free and bound excitons in doped diamond. *Physical Review B*, **2016**, 93,	3.3	7
183	Transport of indirect excitons in ZnO quantum wells. *Optics Letters*, **2015**, 40, 3667-70	3	13
182	Transport of dipolar excitons in (Al,Ga)N/GaN quantum wells. *Physical Review B*, **2015**, 91,	3.3	16
181	VIS-UV ZnCdO/ZnO multiple quantum well nanowires and the quantification of Cd diffusion. *Nanotechnology*, **2014**, 25, 255202	3.4	7
180	Advances in MBE Selective Area Growth of III-Nitride Nanostructures: From NanoLEDs to Pseudo Substrates. *International Journal of High Speed Electronics and Systems*, **2014**, 23, 1450020	0.5	4
179	Sub-meV linewidth in GaN nanowire ensembles: Absence of surface excitons due to the field ionization of donors. *Physical Review B*, **2014**, 90,	3.3	25
178	Transient photoluminescence of aluminum-rich (Al,Ga)N low-dimensional structures. *Physica Status Solidi (A) Applications and Materials Science*, **2014**, 211, 765-768	1.6	5
177	Surface-Related Optical Properties of GaN-Based Nanowires **2014**, 59-79		1
176	Light-emitting-diodes based on ordered InGaN nanocolumns emitting in the blue, green and yellow spectral range. *Nanotechnology*, **2014**, 25, 435203	3.4	18
175	Three-dimensional magneto-photoluminescence as a probe of the electronic properties of crystal-phase quantum disks in GaAs nanowires. *Nano Letters*, **2013**, 13, 5303-10	11.5	26
174	Optical properties and microstructure of 2.02-3.30 eV ZnCdO nanowires: Effect of thermal annealing. *Applied Physics Letters*, **2013**, 102, 143103	3.4	14
173	Temperature-Dependence of Exciton Radiative Recombination in (Al,Ga)N/GaN Quantum Wells Grown ona-Plane GaN Substrates. *Japanese Journal of Applied Physics*, **2013**, 52, 08JC01	1.4	8
172	Oxygen photo-adsorption related quenching of photoluminescence in group-III nitride nanocolumns. *Superlattices and Microstructures*, **2012**, 52, 165-171	2.8	12
171	Thermal carrier emission and nonradiative recombinations in nonpolar (Al,Ga)N/GaN quantum wells grown on bulk GaN. *Journal of Applied Physics*, **2012**, 111, 033517	2.5	10

170	E-beam nano-patterning for the ordered growth of GaN/InGaN nanorods. *Microelectronic Engineering*, **2012**, 98, 374-377	2.5	3
169	Importance of excitonic effects and the question of internal electric fields in stacking faults and crystal phase quantum discs: The model-case of GaN. *Journal of Applied Physics*, **2012**, 112, 053512	2.5	21
168	Impact of biexcitons on the relaxation mechanisms of polaritons in III-nitride based multiple quantum well microcavities. *Physical Review B*, **2012**, 85,	3.3	13
167	ORDERED GAN/INGAN NANORODS ARRAYS GROWN BY MOLECULAR BEAM EPITAXY FOR PHOSPHOR-FREE WHITE LIGHT EMISSION. *International Journal of High Speed Electronics and Systems*, **2012**, 21, 1250010	0.5	7
166	Selective area growth and characterization of InGaN nano-disks implemented in GaN nanocolumns with different top morphologies. *Applied Physics Letters*, **2012**, 100, 231906	3.4	33
165	One-dimensional exciton luminescence induced by extended defects in nonpolar GaN/(Al,Ga)N quantum wells. *Semiconductor Science and Technology*, **2011**, 26, 025012	1.8	15
164	Time-resolved cathodoluminescence on polychromatic light emitting (In,Ga)N quantum wells grown on (11-22) GaN facets. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1394-1397		5
163	Radiative defects in GaN nanocolumns: Correlation with growth conditions and sample morphology. *Applied Physics Letters*, **2011**, 98, 083104	3.4	31
162	Intrinsic dynamics of weakly and strongly confined excitons in nonpolar nitride-based heterostructures. *Physical Review B*, **2011**, 83,	3.3	26
161	Emission control of InGaN nanocolumns grown by molecular-beam epitaxy on Si(111) substrates. *Applied Physics Letters*, **2011**, 99, 131108	3.4	28
160	Exciton recombination dynamics in a-plane (Al,Ga)N/GaN quantum wells probed by picosecond photo and cathodoluminescence. *Journal of Applied Physics*, **2010**, 107, 043524	2.5	30
159	Time-resolved spectroscopy on GaN nanocolumns grown by plasma assisted molecular beam epitaxy on Si substrates. *Journal of Applied Physics*, **2009**, 105, 013113	2.5	55
158	Low-temperature time-resolved cathodoluminescence study of exciton dynamics involving basal stacking faults in a-plane GaN. *Applied Physics Letters*, **2009**, 94, 201115	3.4	39
157	Electron localization by a donor in the vicinity of a basal stacking fault in GaN. *Physical Review B*, **2009**, 80,	3.3	24
156	Exciton localization on basal stacking faults in a-plane epitaxial lateral overgrown GaN grown by hydride vapor phase epitaxy. *Journal of Applied Physics*, **2009**, 105, 043102	2.5	65
155	Comparison of strong coupling regimes in bulk GaAs, GaN, and ZnO semiconductor microcavities. *Physical Review B*, **2008**, 78,	3.3	45
154	Polarized emission from GaN/AlN quantum dots: Single-dot spectroscopy and symmetry-based theory. *Physical Review B*, **2008**, 77,	3.3	57
153	Optical properties of GaN/AlN quantum dots. *Comptes Rendus Physique*, **2008**, 9, 816-829	1.4	12

152	Time-resolved photoluminescence and optically stimulated luminescence measurements of picosecond-excited SrS:Ce,Sm phosphor. *Journal of Applied Physics*, **2007**, 102, 123102	2.5	7
151	Contribution of long lived metastable states to the PL of InP dots in indirect band-gap barrier layers. *EPJ Applied Physics*, **2007**, 37, 15-18	1.1	2
150	Radiative lifetime in wurtzite GaN/AlN quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 183-186		1
149	Time-resolved spectroscopy of excitonic transitions in ZnO/(Zn, Mg)O quantum wells. *Superlattices and Microstructures*, **2007**, 41, 352-359	2.8	12
148	Investigation of Non-Radiative Processes in InAs/(Ga,In)(N,As) Quantum Dots. *Japanese Journal of Applied Physics*, **2007**, 46, L317-L319	1.4	2
147	Barrier composition dependence of the internal electric field in ZnO□n1□MgxO quantum wells. *Applied Physics Letters*, **2007**, 90, 201912	3.4	63
146	Spin-exchange interaction in ZnO-based quantum wells. *Physical Review B*, **2006**, 74,	3.3	25
145	Photoluminescence of single GaN□lN hexagonal quantum dots on Si(111): Spectral diffusion effects. *Physical Review B*, **2006**, 74,	3.3	53
144	Strong potential profile fluctuations and effective localization process in InGaN□aN multiple quantum wells grown on {10-1m} faceted surface GaN template. *Journal of Applied Physics*, **2006**, 100, 013528	2.5	4
143	Radiative lifetime of a single electron-hole pair in GaN□lN quantum dots. *Physical Review B*, **2006**, 73,	3.3	101
142	Time resolved photoluminescence study of ZnO/(Zn,Mg)O quantum wells. *Journal of Crystal Growth* , **2006**, 287, 12-15	1.6	22
141	k.P energy-band structure of ZnO/Zn1□MgxO quantum well heterostructures. *Superlattices and Microstructures*, **2006**, 39, 91-96	2.8	23
140	Optical properties of ZnO nanorods and nanowires. *Superlattices and Microstructures*, **2006**, 39, 358-365	2.8	13
139	Internal electric field in wurtzite ZnO□n0.78Mg0.22O quantum wells. *Physical Review B*, **2005**, 72,	3.3	191
138	Longitudinal-optical phonon broadening due to nitrogen atom incorporation in InGaAsN/GaAs quantum wells. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 3887-3890		2
137	Enhancement of localization and confinement effects in quaternary group-III nitride multi-quantum wells on SiC substrate. *Physica Status Solidi (A) Applications and Materials Science*, **2005**, 202, 642-646	1.6	1
136	Continuous wave and time resolved spectroscopy of InAsN/GaAsN based quantum dots. *Physica Status Solidi (A) Applications and Materials Science*, **2005**, 202, 2598-2603	1.6	3
135	Localization Effects in InGaN/GaN Double Heterostructure Laser Diode Structures Grown on Bulk GaN Crystals. *Japanese Journal of Applied Physics*, **2005**, 44, 7244-7249	1.4	2

134	Morphology Control of ZnO Nanomaterials using Double Hydrophilic Block Copolymers. *Materials Research Society Symposia Proceedings*, **2005**, 901, 1		
133	Efficient radiative recombination and potential profile fluctuations in low-dislocation InGaN□GaN multiple quantum wells on bulk GaN substrates. *Journal of Applied Physics*, **2005**, 97, 103507	2.5	20
132	Observation and modeling of the time-dependent descreening of internal electric field in a wurtzite GaN/Al0.15Ga0.85N quantum well after high photoexcitation. *Physical Review B*, **2004**, 69,	3.3	48
131	Carrier recombination processes in GaAsN: from the dilute limit to alloying. *IEE Proceedings: Optoelectronics*, **2004**, 151, 365-368		4
130	Surprisingly low built-in electric fields in quaternary AlInGaN heterostructures. *Physica Status Solidi A*, **2004**, 201, 190-194		3
129	Nontrivial carrier recombination dynamics and optical properties of over-excited GaN/AlN quantum dots. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 2779-2782	1.3	1
128	Micro-photoluminescence of GaN quantum dots embedded in 100 nm wide cylindrical AlN pillars. *Superlattices and Microstructures*, **2004**, 36, 783-790	2.8	1
127	From GaAs:N to oversaturated GaAsN: Analysis of the band-gap reduction. *Physical Review B*, **2004**, 69,	3.3	32
126	Photoluminescence energy and linewidth in GaN/AlN stackings of quantum dot planes. *Journal of Applied Physics*, **2004**, 96, 180-185	2.5	39
125	Small Internal Electric Fields in Quaternary InAlGaN Heterostructures **2004**, 215-222		
124	Two-dimensional □pseudo-donor□acceptor-pairs□model of recombination dynamics in InGaN/GaN quantum wells. *Physica E: Low-Dimensional Systems and Nanostructures*, **2003**, 17, 64-67	3	7
123	Photo-induced interband absorption in group-III nitride quantum wells. *Physica E: Low-Dimensional Systems and Nanostructures*, **2003**, 17, 247-249	3	
122	Optical properties of GaN/AlN quantum boxes under high photo-excitation. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 2666-2669		1
121	Coexistence in photoluminescence of free exciton and bound exciton in low nitrogen content GaInNAs layers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 2631-2634		
120	Donor-acceptor-like behavior of electron-hole pair recombinations in low-dimensional (Ga,In)N/GaN systems. *Physical Review B*, **2003**, 68,	3.3	84
119	Time dependence of the photoluminescence of GaN/AlN quantum dots under high photoexcitation. *Physical Review B*, **2003**, 68,	3.3	38
118	Nonlinear behavior of photoabsorption in hexagonal nitride quantum wells due to free carrier screening of the internal fields. *Physical Review B*, **2003**, 67,	3.3	36
117	Determination of built-in electric fields in quaternary InAlGaN heterostructures. *Applied Physics Letters*, **2003**, 82, 1541-1543	3.4	21

116	Isoelectronic traps in heavily doped GaAs:(In,N). *Physical Review B*, **2003**, 68,	3.3	14
115	Small Built-in Electric Fields in Quaternary InAlGaN Heterostructures. *Physica Status Solidi (B): Basic Research*, **2002**, 234, 764-768	1.3	1
114	Light-Hole and Heavy-Hole Excitons: the Right Probe for the Physics of Low N Content GaAsN. *Physica Status Solidi (B): Basic Research*, **2002**, 234, 778-781	1.3	1
113	The Effects of Localization and of Electric Fields on LO-Phonon□Exciton Coupling in InGaN/GaN Quantum Wells and Quantum Boxes. *Physica Status Solidi A*, **2002**, 190, 149-154		14
112	Photoluminescence of Excitons in InxGa1□xN/InyGa1□yN Multiple Quantum Wells. *Physica Status Solidi A*, **2002**, 190, 161-166		1
111	Time-resolved spectroscopy of (Al,Ga,In)N based quantum wells: Localization effects and effective reduction of internal electric fields. *Physical Review B*, **2002**, 66,	3.3	18
110	Micro Epitaxial lateral overgrowth of GaN/sapphire by Metal Organic Vapour Phase Epitaxy. *MRS Internet Journal of Nitride Semiconductor Research*, **2002**, 7, 1		66
109	Self-Induced Photon Absorption by Screening of the Electric Fields in Nitride-based Quantum Wells. *Materials Research Society Symposia Proceedings*, **2002**, 743, L11.5.1		
108	Microscopic Description of Radiative Recombinations in InGaN/GaN Quantum Systems. *Materials Research Society Symposia Proceedings*, **2002**, 743, L5.5.1		1
107	Large size dependence of exciton-longitudinal-optical-phonon coupling in nitride-based quantum wells and quantum boxes. *Applied Physics Letters*, **2002**, 80, 428-430	3.4	62
106	The Effects of Localization and of Electric Fields on LO-Phonon□Exciton Coupling in InGaN/GaN Quantum Wells and Quantum Boxes **2002**, 190, 149		1
105	Cw and time-resolved spectroscopy in homoepitaxial GaN films and GaN□GaAlN quantum wells grown by molecular beam epitaxy. *Solid State Communications*, **2001**, 117, 445-448	1.6	6
104	Time-resolved spectroscopy of MBE-grown GaN/AlGaN hetero- and homo-epitaxial quantum wells. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 82, 140-142	3.1	4
103	Donor binding energies in group III-nitride-based quantum wells: influence of internal electric fields. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 82, 221-223	3.1	9
102	Confined exciton-polariton modes in a thin, homo-epitaxial, GaN film grown by molecular beam epitaxy. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 82, 173-177	3.1	2
101	Optical properties of self-assembled InGaN/GaN quantum dots. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 82, 151-155	3.1	5
100	Dual Contribution to the Stokes Shift in InGaN□GaN Quantum Wells. *Physica Status Solidi (B): Basic Research*, **2001**, 228, 111-114	1.3	9
99	Carrier Dynamics in Group-III Nitride Low-Dimensional Systems: Localization versus Quantum-Confined Stark Effect. *Physica Status Solidi (B): Basic Research*, **2001**, 228, 65-72	1.3	13

98	Reduction of Carrier In-Plane Mobility in Group-III Nitride Based Quantum Wells: The Role of Internal Electric Fields. *Physica Status Solidi A*, **2001**, 183, 61-66		12
97	Influence of electron-phonon interaction on the optical properties of III nitride semiconductors. *Journal of Physics Condensed Matter*, **2001**, 13, 7053-7074	1.8	116
96	Effects of GaAlN barriers and of dimensionality on optical recombination processes in InGaN quantum wells and quantum boxes. *Applied Physics Letters*, **2001**, 78, 1538-1540	3.4	50
95	Exclusion principle and screening of excitons in GaN/AlxGa1□N quantum wells. *Physical Review B*, **2001**, 63,	3.3	24
94	High internal electric field in a graded-width InGaN/GaN quantum well: Accurate determination by time-resolved photoluminescence spectroscopy. *Applied Physics Letters*, **2001**, 78, 1252-1254	3.4	194
93	Carrier relaxation dynamics for As defects in GaN. *Applied Physics Letters*, **2001**, 79, 69-71	3.4	8
92	Optical properties of group-III nitride quantum wells and quantum boxes. *Journal of Physics Condensed Matter*, **2001**, 13, 7027-7042	1.8	18
91	Reduction of Carrier In-Plane Mobility in Group-III Nitride Based Quantum Wells: The Role of Internal Electric Fields **2001**, 183, 61		1
90	Recombination Dynamics in Nitride Quantum Boxes and Quantum Wells for Colors Ranging from the UV to the Red. *Materials Research Society Symposia Proceedings*, **2000**, 639, 1011		1
89	Excitons and Trions Confined on CdTe Nano-Islands: Optical Tuning of the Dielectric Response. *Physica Status Solidi (B): Basic Research*, **2000**, 220, 875-884	1.3	1
88	Time-Resolved Spectroscopy of MBE-Grown Nitride Based Heterostructures. *Physica Status Solidi A*, **2000**, 178, 101-105		3
87	Scale Effects on Exciton Localization and Nonradiative Processes in GaN/AlGaN Quantum Wells. *Physica Status Solidi A*, **2000**, 180, 127-132		32
86	Time-Resolved Spectroscopy of MBE-Grown InGaN/GaN Self-Formed Quantum Dots. *Physica Status Solidi A*, **2000**, 180, 375-380		18
85	Strain effects in GaN epilayers. *Comptes Rendus Physique*, **2000**, 1, 51-60		2
84	Electron-hole plasma effect on excitons in GaN/AlxGa1□N quantum wells. *Physical Review B*, **2000**, 61, 15621-15624	3.3	24
83	Optical properties of GaN epilayers and GaN/AlGaN quantum wells grown by molecular beam epitaxy on GaN(0001) single crystal substrate. *Journal of Applied Physics*, **2000**, 88, 183-187	2.5	39
82	Scale Effects on Exciton Localization and Nonradiative Processes in GaN/AlGaN Quantum Wells **2000**, 180, 127		1
81	Optical and Structural Properties of AlGaN/GaN Quantum Wells Grown by Molecular Beam Epitaxy. *MRS Internet Journal of Nitride Semiconductor Research*, **1999**, 4, 962-967		

80	Photoreflectance investigations of the bowing parameter in AlGaN alloys lattice-matched to GaN. *Applied Physics Letters*, **1999**, 74, 3353-3355	3.4	43
79	Photoreflectance spectroscopy as a powerful tool for the investigation of GaN/AlGaN quantum well structures. *Solid State Communications*, **1999**, 109, 567-571	1.6	9
78	Recombination dynamics of excitons in III-nitride layers and quantum wells. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 59, 307-314	3.1	9
77	Microcalorimetric absorption spectroscopy in GaN/AlGaN quantum wells. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 59, 319-322	3.1	
76	Photoreflectance Spectroscopy Investigation of GaN/AlGaN Quantum Well Structures. *Physica Status Solidi (B): Basic Research*, **1999**, 216, 221-225	1.3	2
75	Slow Spin Relaxation Observed in InGaN/GaN Multiple Quantum Wells. *Physica Status Solidi (B): Basic Research*, **1999**, 216, 341-345	1.3	11
74	Dynamics of Excitons in GaN/AlGaN MQWs with Varying Depths, Thicknesses and Barrier Widths. *Physica Status Solidi (B): Basic Research*, **1999**, 216, 361-364	1.3	20
73	CW and Time-Resolved Optical Spectroscopy of GaN Epilayers and GaN/AlGaN Quantum Wells Grown on A-Plane Sapphire. *Physica Status Solidi (B): Basic Research*, **1999**, 216, 365-369	1.3	2
72	Confined Excitons in GaN/AlGaN Quantum Wells. *Physica Status Solidi (B): Basic Research*, **1999**, 216, 371-374	1.3	51
71	Highly Photo-Excited Nitride Quantum Wells: Threshold for Exciton Bleaching. *Physica Status Solidi (B): Basic Research*, **1999**, 216, 481-486	1.3	3
70	Time-resolved photoluminescence as a probe of internal electric fields in GaN-(GaAl)N quantum wells. *Physical Review B*, **1999**, 59, 15363-15367	3.3	120
69	Barrier-width dependence of group-III nitrides quantum-well transition energies. *Physical Review B*, **1999**, 60, 1496-1499	3.3	168
68	Observation of long-lived oblique excitons in GaN-AlGaN multiple quantum wells. *Physical Review B* , **1999**, 59, 10246-10250	3.3	34
67	Confined Excitons in GaN/AlGaN Quantum Wells **1999**, 216, 371		3
66	Excitons trapped on self-organised CdTe islands in wide ZnTe quantum wells. *Journal of Crystal Growth*, **1998**, 184-185, 288-292	1.6	2
65	Center-of-mass quantization of light- and heavy-hole excitons in wide ZnTe-(Zn,Mg)Te quantum wells. *Journal of Crystal Growth*, **1998**, 184-185, 844-848	1.6	3
64	Quantum confined Stark effect due to built-in internal polarization fields in (Al,Ga)N/GaN quantum wells. *Physical Review B*, **1998**, 58, R13371-R13374	3.3	362
63	Exciton Dynamics of Thick GaN Epilayers Deposited by MOVPE on Al2O3. *Materials Science Forum*, **1998**, 264-268, 1279-1282	0.4	1

62	Optical Properties of InGaN/GaN Multiple Quantum Wells. *Materials Science Forum*, **1998**, 264-268, 1295-1298	0.4	2
61	Recombination dynamics of free and localized excitons in GaN/Ga0.93Al0.07N quantum wells. *Physical Review B*, **1998**, 57, R9447-R9450	3.3	103
60	Optical properties versus growth conditions of CdTe submonolayers inserted in ZnTe quantum wells. *Physical Review B*, **1998**, 58, 15736-15743	3.3	7
59	Charged excitons trapped on monomolecular CdTe islands in wide ZnTe-(Zn,Mg)Te quantum wells. *Physical Review B*, **1998**, 58, 15408-15411	3.3	13
58	Optical studies of ultrashort-period GaAs/AlAs superlattices grown on (In,Ga)As pseudosubstrate. *Physical Review B*, **1998**, 58, R7540-R7543	3.3	1
57	Optical and Structural Properties of AlGaN/GaN Quantum Wells Grown by Molecular Beam Epitaxy. *Materials Research Society Symposia Proceedings*, **1998**, 537, 1		1
56	Quantum-Confined Stark Effect and Recombination Dynamics of Spatially Indirect Excitons in MBE-Grown GaN-AlGaN Quantum Wells. *Materials Research Society Symposia Proceedings*, **1998**, 537, 1		1
55	Optical investigation of CdTe monomolecular islands in wide ZnTe/(Zn,Mg)Te quantum wells: Evidence of a vertical self-ordering. *Physical Review B*, **1997**, 56, 3907-3912	3.3	21
54	Optical absorption of type-II superlattices. *Physical Review B*, **1997**, 55, 15786-15790	3.3	11
53	Analytical model for the refractive index in quantum wells derived from the complex dielectric constant of Wannier excitons in noninteger dimensions. *Journal of Applied Physics*, **1997**, 82, 798-802	2.5	47
52	Distinct center-of-mass quantization of light-hole and heavy-hole excitons in wide ZnTe-(Zn,Mg)Te quantum wells. *Physical Review B*, **1997**, 56, R10040-R10043	3.3	6
51	Time-Resolved Photoluminescence of GaN / Ga0.93Al0.07N Quantum Wells. *Materials Research Society Symposia Proceedings*, **1997**, 482, 642		
50	Time-resolved photoluminescence studies of InGaN/GaN multiple quantum wells. *MRS Internet Journal of Nitride Semiconductor Research*, **1997**, 2, 1		10
49	Dynamics of photoluminescence in medium-size CdSe quantum crystallites. *Semiconductor Science and Technology*, **1997**, 12, 958-965	1.8	15
48	Role of the V/III precursor ratio on exciton dynamics in GaN MOCVD epilayers. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1997**, 50, 201-204	3.1	4
47	Wannier Excitons in Noninteger Dimensions: A Simple Analytical Expression for the Complex Dielectric Constant of Semiconductor Structures. *Physica Status Solidi A*, **1997**, 164, 159-163		4
46	Exciton dynamics in thick GaN MOVPE epilayers deposited on sapphire.. *MRS Internet Journal of Nitride Semiconductor Research*, **1997**, 2, 1		6
45	Quantum wells with zero valence-band offset: Drastic enhancement of forbidden excitonic transitions. *Physical Review B*, **1996**, 54, R11078-R11081	3.3	6

44	Effects of finite spin-orbit splitting on optical properties of spherical semiconductor quantum dots. *Physical Review B*, **1996**, 53, 7287-7298	3.3	66
43	Influence of spin-orbit split-off band on optical properties of spherical semiconductor nanocrystals. The case of CdTe. *Solid State Communications*, **1996**, 98, 303-306	1.6	11
42	Evidence of the ordered growth of monomolecular ZnTe islands in CdTe/(Cd,Zn)Te quantum wells on a nominal (001) surface. *Physical Review B*, **1996**, 53, R16164-R16167	3.3	11
41	Measurement of the optical band gap and crystal-field splitting in wurtzite CdTe. *Physical Review B*, **1996**, 53, 15440-15442	3.3	18
40	Confined excitons in semiconductors: Correlation between binding energy and spectral absorption shape. *Physical Review B*, **1995**, 52, 5756-5759	3.3	52
39	Quantum confinement effects of CdS nanocrystals in a sodium borosilicate glass prepared by the sol-gel process. *Journal of Applied Physics*, **1995**, 77, 287-293	2.5	67
38	Universal formulation of excitonic linear absorption spectra in all semiconductor microstructures. *Superlattices and Microstructures*, **1995**, 17, 19-21	2.8	9
37	Sol-gel preparation and optical characterization of sodium borosilicate glasses doped with II-VI semiconductor nanocrystals **1994**,		1
36	New elaboration of Na2O-B2O3-SiO2 glass doped with CdS nanocrystals from gel formed in aqueous solution. *Journal of Sol-Gel Science and Technology*, **1994**, 2, 765-769	2.3	5
35	Structural investigations of InGaAs/InGaAs SLSs for optoelectronic device applications. *Superlattices and Microstructures*, **1994**, 15, 187	2.8	2
34	Optical properties of II-VI semiconductor nanocrystals produced by sol-gel synthesis in sodium borosilicate glasses. *Superlattices and Microstructures*, **1994**, 15, 447-451	2.8	16
33	Elastic characterization of porous silicon by acoustic microscopy. *Superlattices and Microstructures*, **1994**, 16, 21-23	2.8	12
32	Absorption properties of CdS nanocrystals in glasses; evidence of both weak and strong confinement regimes. *Journal of Crystal Growth*, **1994**, 138, 998-1003	1.6	32
31	A single equation describes excitonic absorption spectra in all quantum-sized semiconductors. *IEEE Journal of Quantum Electronics*, **1994**, 30, 2287-2292	2	21
30	Improved modeling of excitons in type-II semiconductor heterostructures by use of a three-dimensional variational function. *Physical Review B*, **1994**, 50, 11840-11844	3.3	25
29	Preparation of II-VI Semiconductor Nanocrystallites in a Glass Matrix Using Chalcogenizing Agent: Application to CdSe. *Materials Research Society Symposia Proceedings*, **1994**, 346, 901		
28	Fractional-dimensional calculation of exciton binding energies in semiconductor quantum wells and quantum-well wires. *Journal of Applied Physics*, **1993**, 74, 5626-5637	2.5	80
27	Uniaxial-stress investigation of asymmetrical GaAs-(Ga,Al)As double quantum wells. *Physical Review B*, **1993**, 47, 1954-1960	3.3	14

26	Unified formulation of excitonic absorption spectra of semiconductor quantum wells, superlattices, and quantum wires. *Physical Review B*, **1993**, 48, 17308-17315	3.3	86
25	Piezoreflectivity investigation of CdTe/(Cd,Zn)Te heterostructures. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1993**, 16, 87-91	3.1	6
24	Influence of the spin-orbit split-off valence band in InxGa1-xAs/AlyGa1-yAs strained-layer quantum wells. *Physical Review B*, **1992**, 45, 3906-3909	3.3	10
23	Excitons in semiconductor superlattices: Heuristic description of the transfer between Wannier-like and Frenkel-like regimes. *Physical Review B*, **1992**, 46, 13603-13606	3.3	42
22	Excitons in semiconductor quantum wells: A straightforward analytical calculation. *Journal of Applied Physics*, **1992**, 72, 300-302	2.5	48
21	Studies of electronic structures of GaAs-(GaAlAs) quantum wells grown on (1l3)-oriented GaAS, under uniaxial stress. *High Pressure Research*, **1992**, 9, 93-96	1.6	
20	Simple analytical method for calculating exciton binding energies in semiconductor quantum wells. *Physical Review B*, **1992**, 46, 4092-4101	3.3	256
19	Optical properties of InGaAs films embedded in plasma etched InP wells. *Applied Physics Letters*, **1992**, 61, 798-800	3.4	3
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13	Electronic structure of (1 1 3)-grown GaAs-(GaAl)As single quantum wells under biaxial strain fields. *Solid State Communications*, **1990**, 75, 677-682	1.6	14
12	Reflectance study of interwell couplings in GaAs-Ga1-xAlxAs double quantum wells. *Physical Review B*, **1990**, 42, 3435-3443	3.3	15
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9	Band offsets and lattice-mismatch effects in strained-layer CdTe/ZnTe superlattices. *Physical Review B*, **1988**, 38, 7740-7748	3.3	68

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1	Microstructures III-V sous pression hydrostatique. *Revue De Physique Appliquée*, **1987**, 22, 859-866		